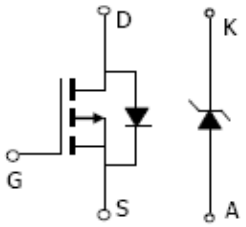
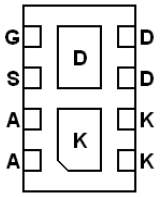
DESCRIPTION

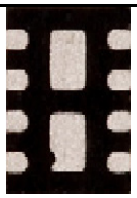
The SSF4703 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge . A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications.



Schematic diagram



Marking and pin Assignment



DFN2X3-8L Bottom View

GENERAL FEATURES

- **MOSFET**
  V_{DS} = -20V,I_D = -3.4A
  $R_{DS(ON)}$ < 160mΩ @ V_{GS}=-1.8V
  $R_{DS(ON)}$ < 120mΩ @ V_{GS}=-2.5V
  $R_{DS(ON)}$ < 90mΩ @ V_{GS}=-4.5V
- **SCHOTTKY**
  V_R = 20V, I_F = 1A, V_F<0.5V @ 0.5A

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- DC-DC conversion applications
- Load switch
- Power management

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
4703	SSF4703	DFN2X3-8L	—	—	—

ABSOLUTE MAXIMUM RATINGS(TA=25℃unless otherwise noted)

Parameter	Symbol	MOSFET	Schottky	Unit
Drain-Source Voltage	V_{DS}	-20		V
Gate-Source Voltage	V_{GS}	±8		V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	-3.4		A
	I_{DM}	-15		A
Schottky reverse voltage	V_R		20	V
Continuous Forward Current	I_F		1.9	A
Pulsed Forward Current	I_{FM}		7	A
Maximum Power Dissipation	P_D	1.7	0.96	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	-55 To 150	℃

THERMAL CHARACTERISTICS

MOSFET			
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	75	℃/W

Schottky			
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	℃/W

ELECTRICAL CHARACTERISTICS (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V,V_{GS}=0V			-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±8V,V_{DS}=0V			±100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-0.45	-0.7	-1	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-3.4A		73	90	mΩ
		V_{GS}=-2.5V, I_D=-2.5A		99	120	
		V_{GS}=-1.8V, I_D=-1.5A		133	160	
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-3.4A	4	7		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-10V,V_{GS}=0V, F=1.0MHz		540		PF
Output Capacitance	C_{oss}			70		PF
Reverse Transfer Capacitance	C_{rss}			50		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-10V,I_D=-3.4A V_{GS}=-4.5V,R_{GEN}=3Ω		10		nS
Turn-on Rise Time	t_r			12		nS
Turn-Off Delay Time	$t_{d(off)}$			44		nS
Turn-Off Fall Time	t_f			22		nS
Total Gate Charge	Q_g	V_{DS}=-10V,I_D=-3.4A,V_{GS}=-4.5V		6.1		nC
Gate-Source Charge	Q_{gs}			0.6		nC
Gate-Drain Charge	Q_{gd}			1.6		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-1A		-0.83	-1	V
Diode Forward Current (Note 2)	I_S				-2	A
SCHOTTKY PARAMETERS						
Forward Voltage Drop	V_F	I_F=0.5A		0.39	0.5	V
Maximum reverse leakage current	Irm	V_R=16V			0.1	mA
Junction Capacitance	C_T	V_R=10V		34		pF
Schottky Reverse Recovery Time	trr	I_F=1A, dI/dt=100A/μs		5.2	10	ns
Schottky Reverse Recovery Charge	Qrr	I_F=1A, dI/dt=100A/μs		0.8		nC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

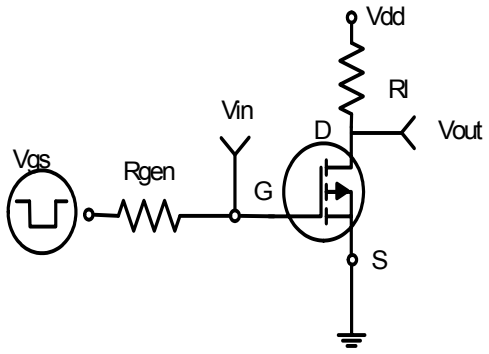


Figure1:Switching Test Circuit

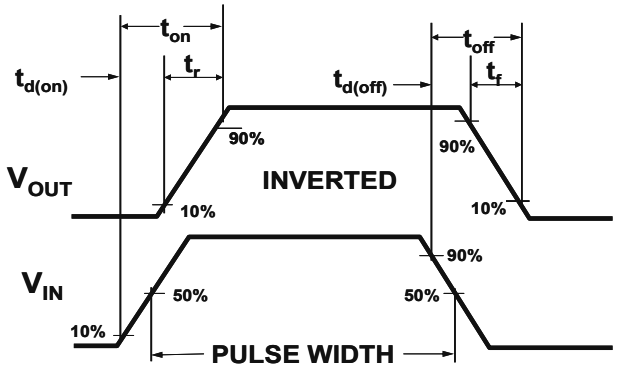


Figure 2:Switching Waveforms

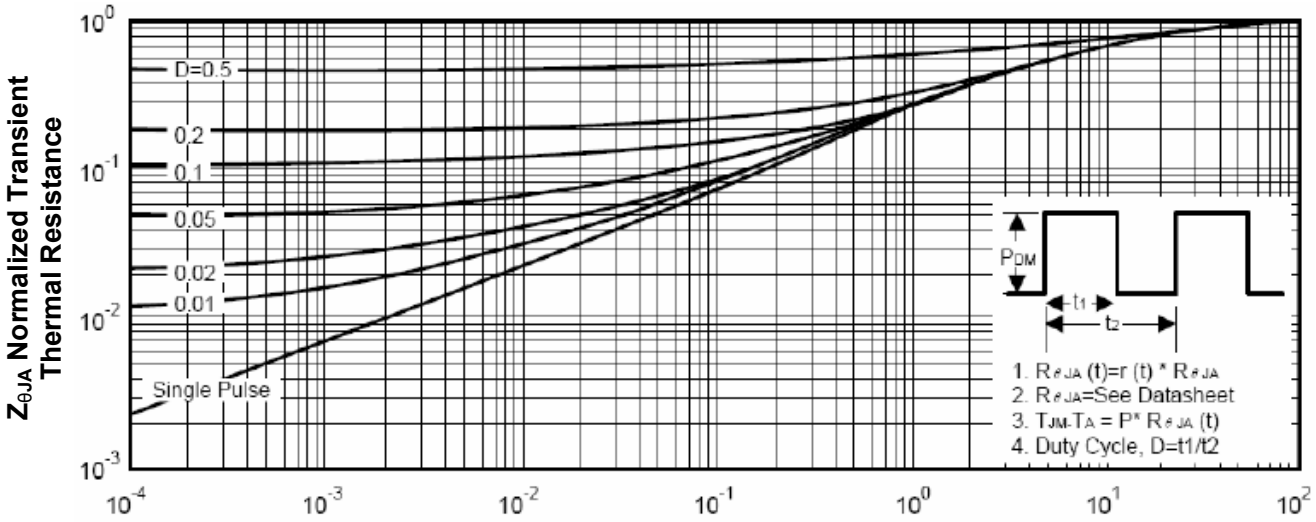
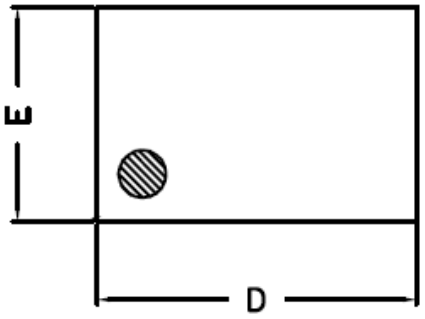


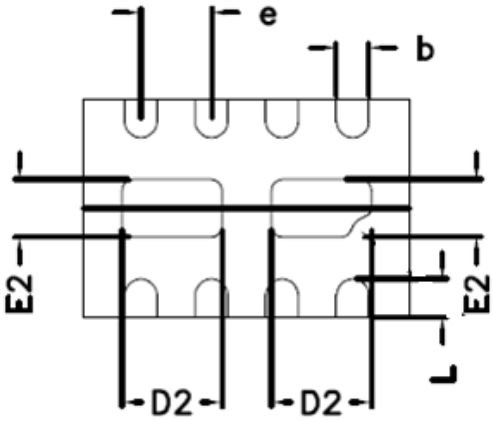
Figure 3: Normalized Maximum Transient Thermal Impedanc

DFN2X3-8L PACKAGE INFORMATION

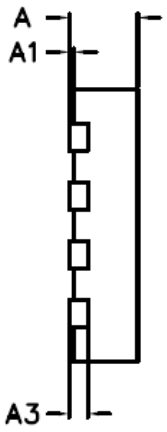
Dimensions in Millimeters (UNIT:mm)



Top View



Bottom View



Side View

COMMON DIMENSIONS(MM)			
PKG.	W:VERY VERY THIN		
REF.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	—	0.05
A3	0.2 REF.		
D	2.95	3.00	3.05
E	1.95	2.00	2.05
b	0.25	0.30	0.35
L	0.25	0.35	0.45
D2	0.77	0.92	1.02
E2	0.38	0.53	0.63
e	0.65 BCS.		

NOTES：

1. All dimensions are in millimeters.
2. Tolerance ±0.10mm (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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